

**Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 2)**
- **ESD Protected Up to 2.5kV**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

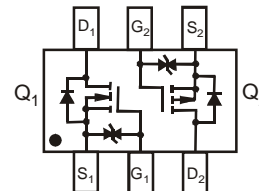
- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 7
- Ordering Information: See Page 7
- Weight: 0.006 grams (approximate)



ESD PROTECTED



TOP VIEW


 TOP VIEW  
Internal Schematic

**Maximum Ratings N-CHANNEL – Q<sub>1</sub>** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±6	V
Drain Current (Note 1)	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	I <sub>D</sub>	1066 690	mA

**Maximum Ratings P-CHANNEL – Q<sub>2</sub>** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±6	V
Drain Current (Note 1)	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 85°C	I <sub>D</sub>	845 548	mA

**Thermal Characteristics – Total Device** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P <sub>D</sub>	330	mW
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>θJA</sub>	379	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB with minimum recommended pad layout.
  2. No purposefully added lead.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).

**Electrical Characteristics N-CHANNEL – Q<sub>1</sub>** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	100	nA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±1.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	-	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	0.3	0.45	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 600mA
			0.4	0.6		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 500mA
			0.5	0.75		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 350mA
Forward Transfer Admittance	Y <sub>fs</sub>	-	1.4	-	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 400mA
Diode Forward Voltage (Note 4)	V <sub>SD</sub>	-	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 150mA
<b>DYNAMIC CHARACTERISTICS (Note 5)</b>						
Input Capacitance	C <sub>iss</sub>	-	60.67	-	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	9.68	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	5.37	-	pF	
Total Gate Charge	Q <sub>g</sub>	-	736.6	-	pC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	-	93.6	-	pC	
Gate-Drain Charge	Q <sub>gd</sub>	-	116.6	-	pC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>L</sub> = 47Ω, R <sub>G</sub> = 10Ω
Turn-On Rise Time	t <sub>r</sub>	-	7.4	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	26.7	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	12.3	-	ns	

**Electrical Characteristics P-CHANNEL – Q<sub>2</sub>** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	-100	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±2.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	0.5	0.75	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -430mA
			0.7	1.05		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
			1.0	1.5		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -150mA
Forward Transfer Admittance	Y <sub>fs</sub>	-	0.9	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA
Diode Forward Voltage (Note 4)	V <sub>SD</sub>	-	-0.8	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -150mA
<b>DYNAMIC CHARACTERISTICS (Note 5)</b>						
Input Capacitance	C <sub>iss</sub>	-	59.76	-	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	12.07	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	6.36	-	pF	
Total Gate Charge	Q <sub>g</sub>	-	622.4	-	pC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA
Gate-Source Charge	Q <sub>gs</sub>	-	100.3	-	pC	
Gate-Drain Charge	Q <sub>gd</sub>	-	132.2	-	pC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 47Ω, R <sub>G</sub> = 10Ω
Turn-On Rise Time	t <sub>r</sub>	-	8.1	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.4	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	20.7	-	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.  
5. Guaranteed by design. Not subject to production testing.

**N-CHANNEL – Q<sub>1</sub>**

NEW PRODUCT

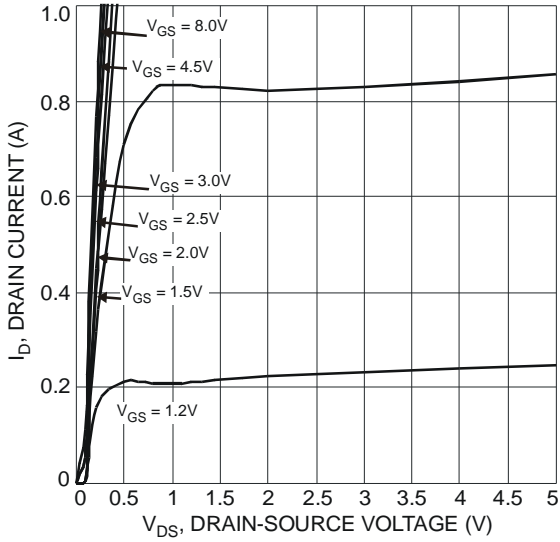


Fig. 1 Typical Output Characteristic

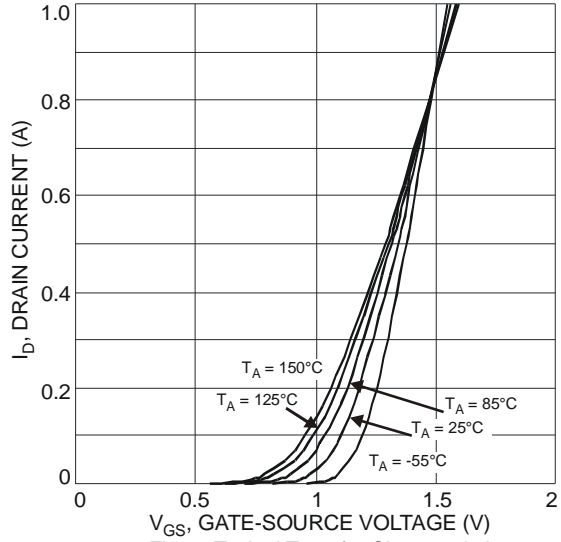


Fig. 2 Typical Transfer Characteristic

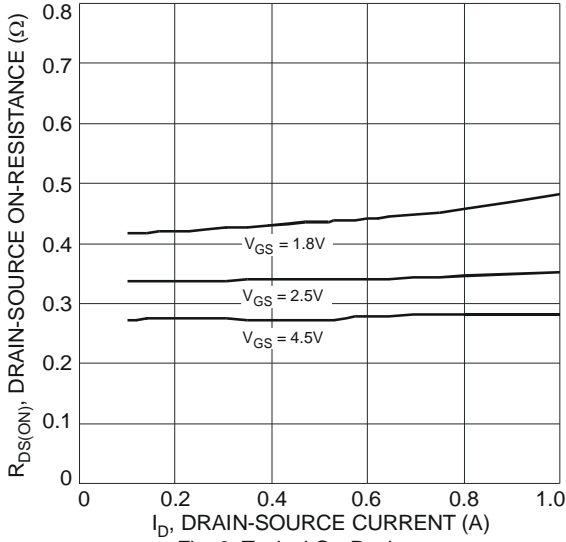


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

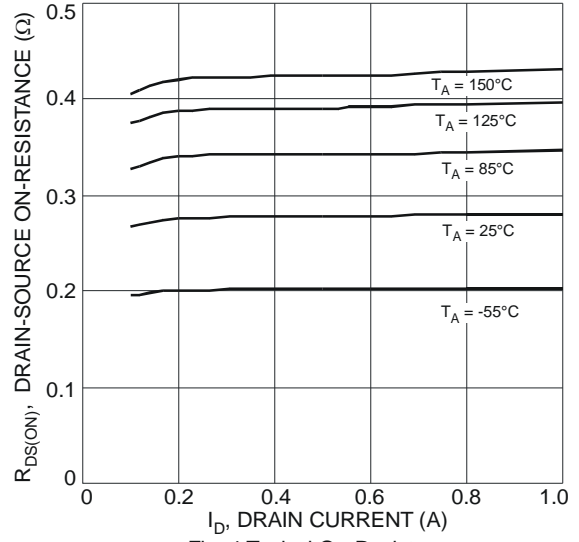


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

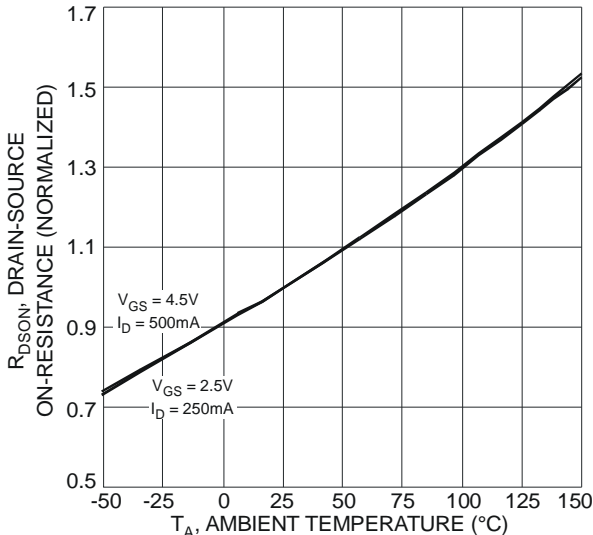


Fig. 5 On-Resistance Variation with Temperature

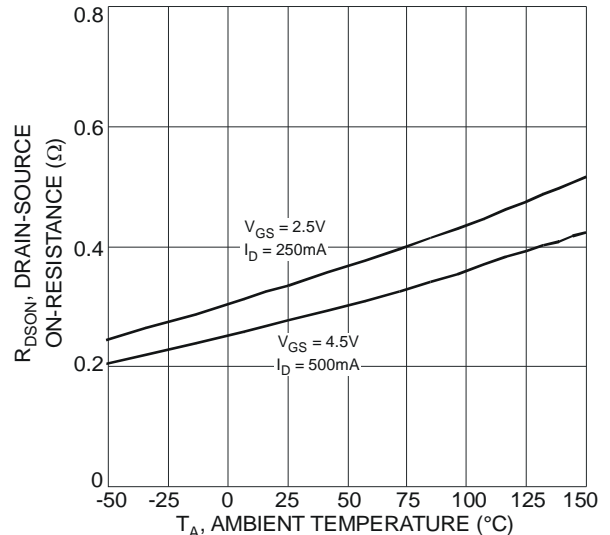


Fig. 6 On-Resistance Variation with Temperature

**N-CHANNEL – Q<sub>1</sub> (continued)**

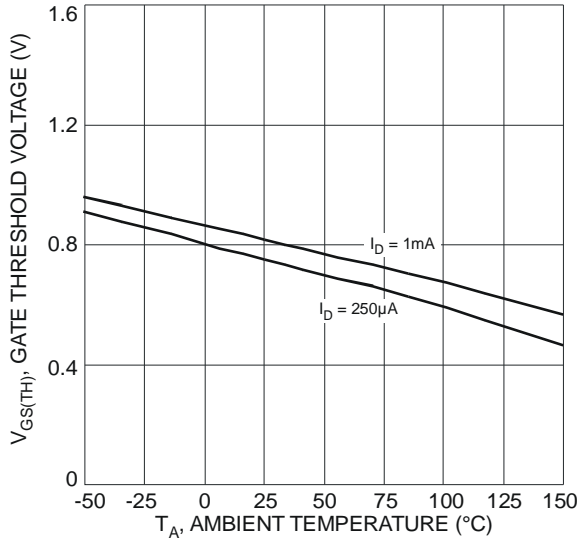


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

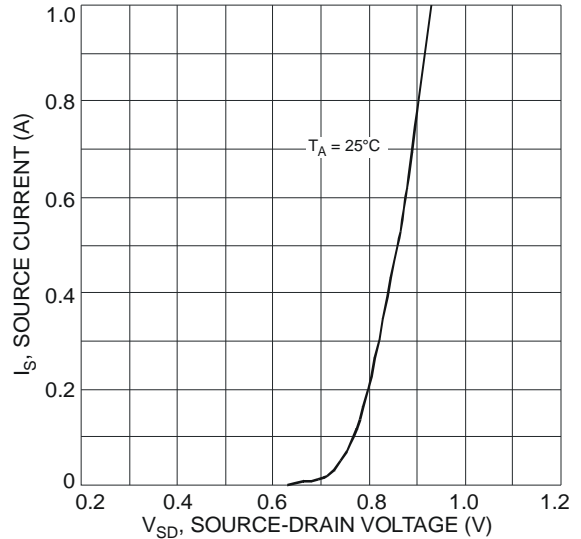


Fig. 8 Diode Forward Voltage vs. Current

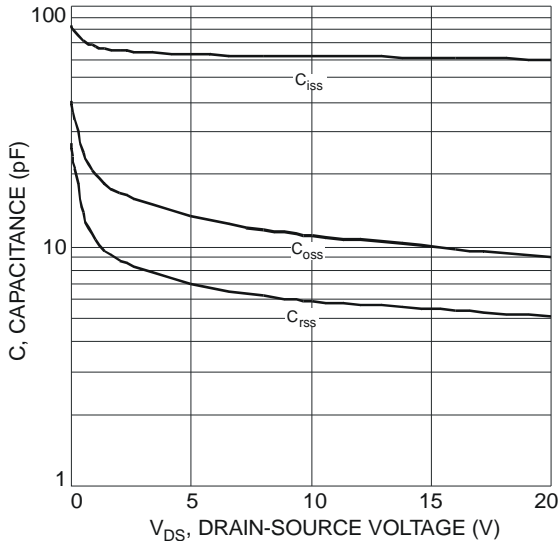


Fig. 9 Typical Total Capacitance

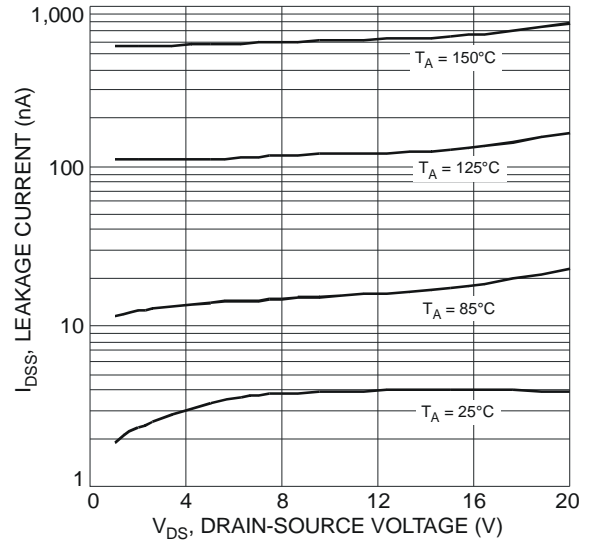


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

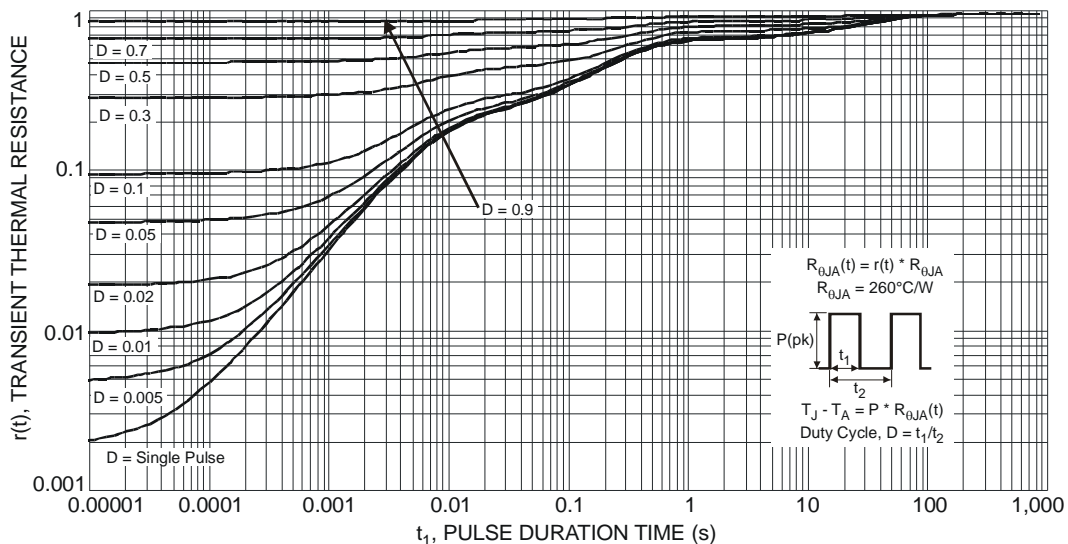


Fig. 11 Transient Thermal Response

**P-CHANNEL – Q<sub>2</sub>**

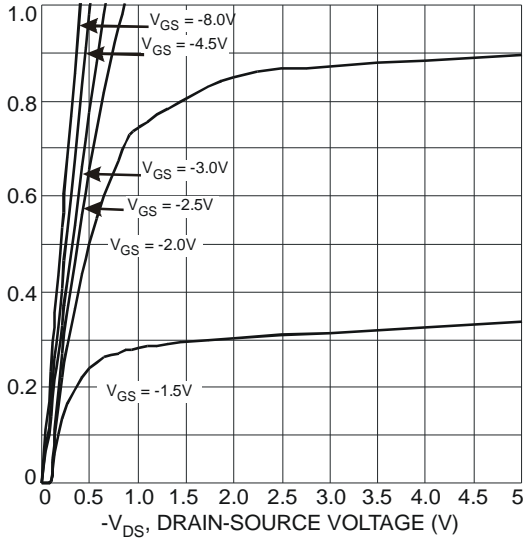


Fig. 12 Typical Output Characteristic

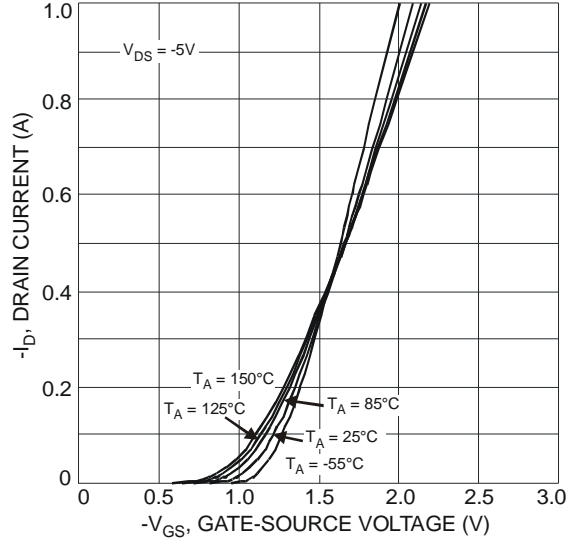


Fig. 13 Typical Transfer Characteristic

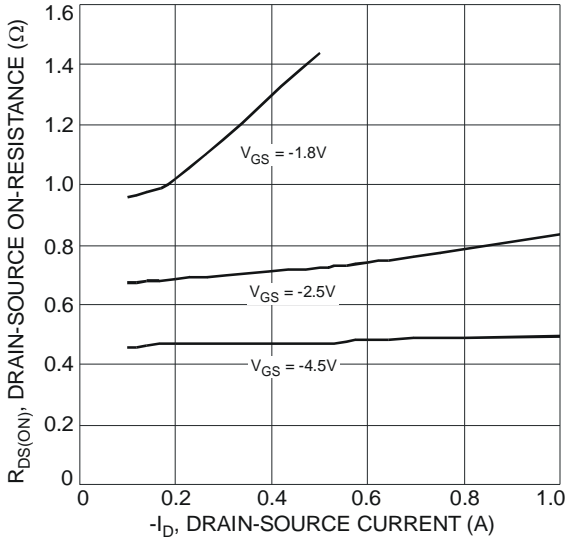


Fig. 14 Typical On-Resistance vs. Drain Current and Gate Voltage

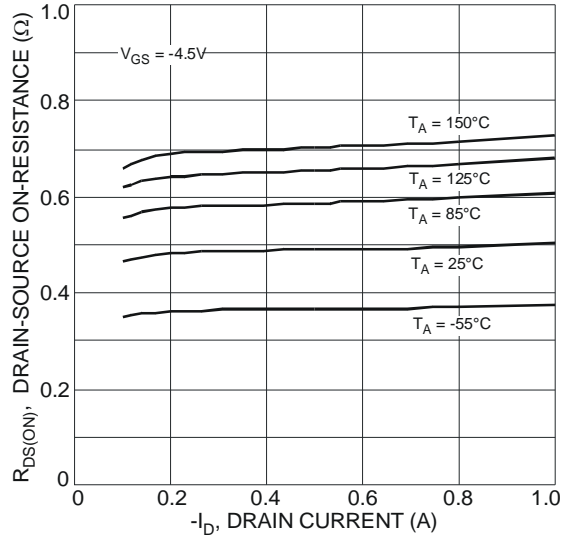


Fig. 15 Typical On-Resistance vs. Drain Current and Temperature

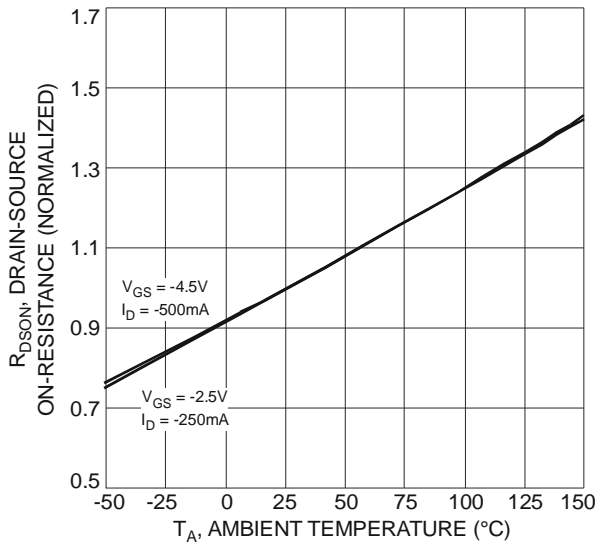


Fig. 16 On-Resistance Variation with Temperature

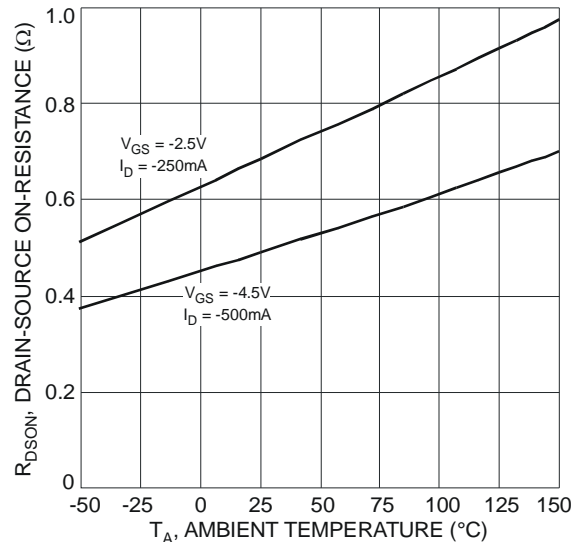


Fig. 17 On-Resistance Variation with Temperature

**P-CHANNEL – Q<sub>2</sub> (continued)**

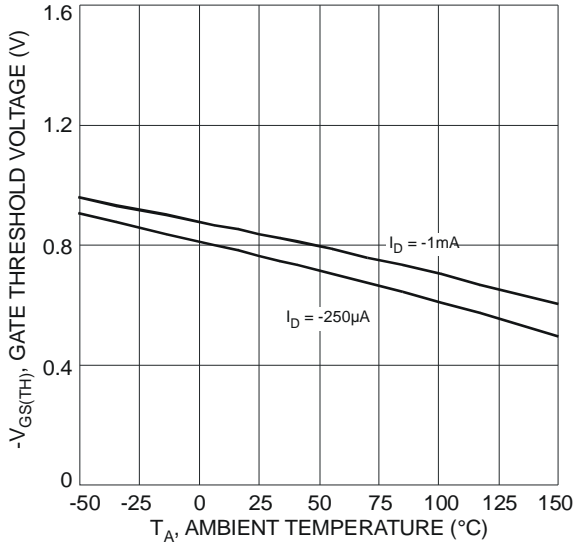


Fig. 18 Gate Threshold Variation vs. Ambient Temperature

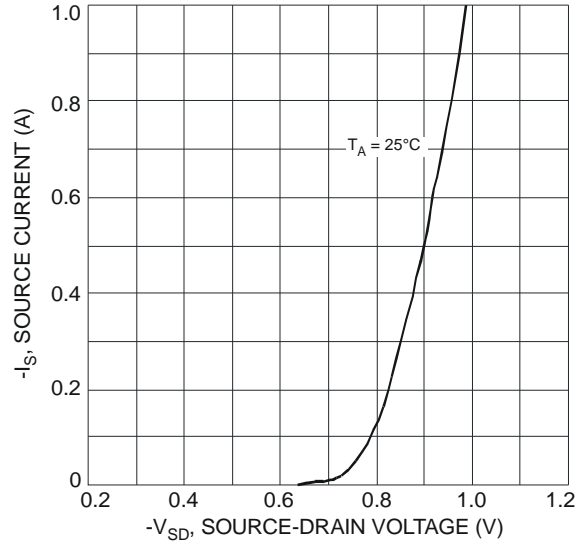


Fig. 19 Diode Forward Voltage vs. Current

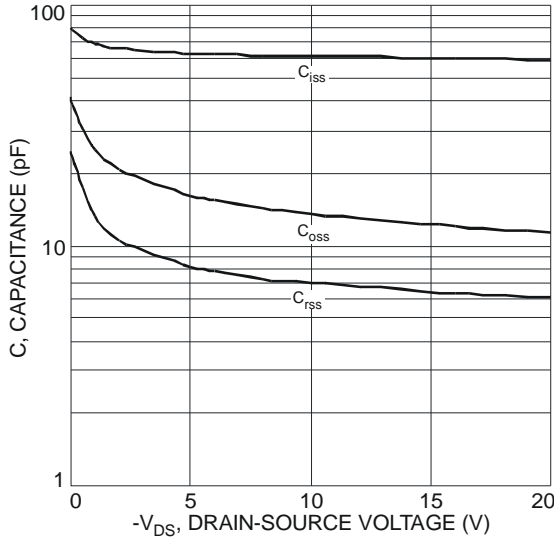


Fig. 20 Typical Total Capacitance

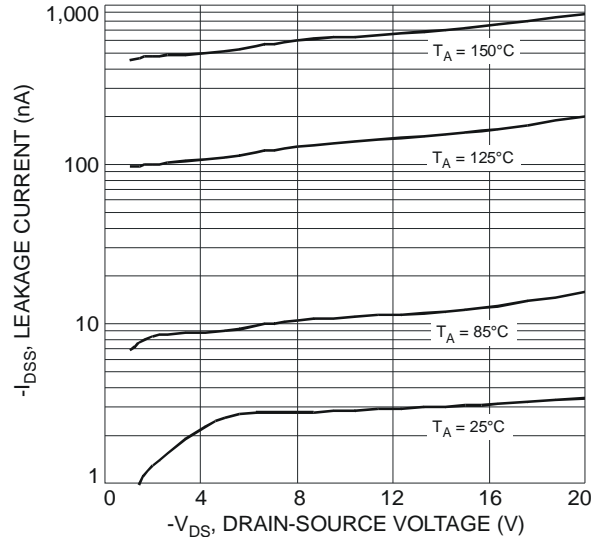


Fig. 21 Typical Leakage Current vs. Drain-Source Voltage

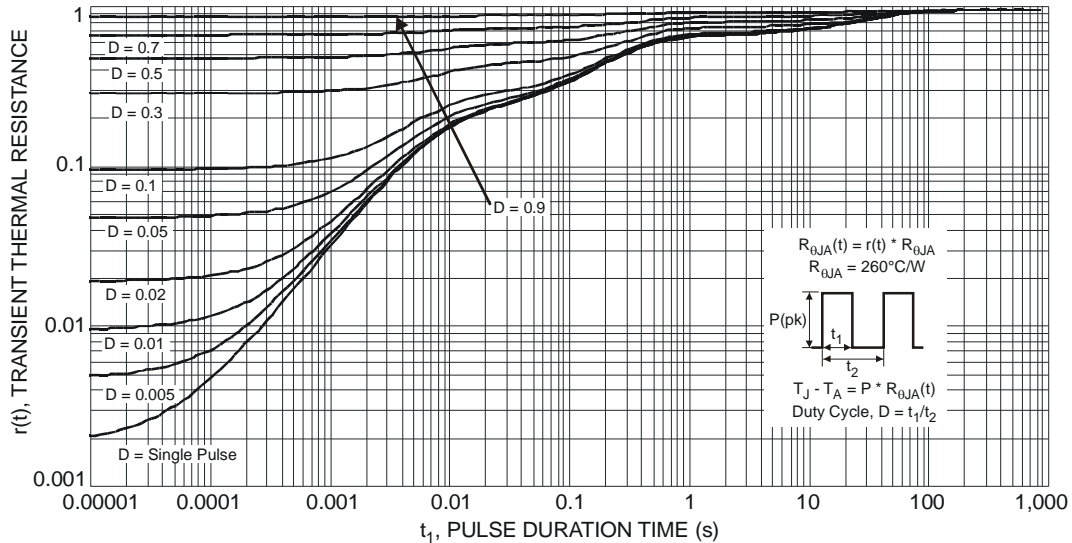


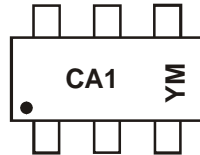
Fig. 22 Transient Thermal Response

**Ordering Information** (Note 6)

Part Number	Case	Packaging
DMG1016UDW-7	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



CA1 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: W = 2009)  
 M = Month (ex: 9 = September)

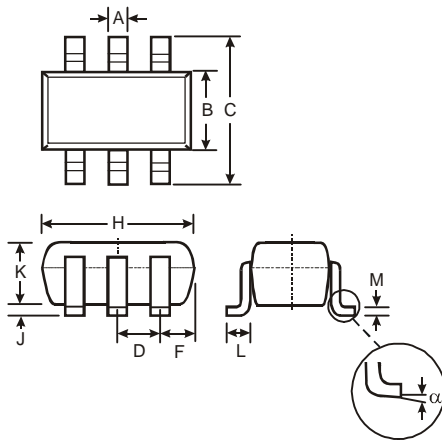
Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

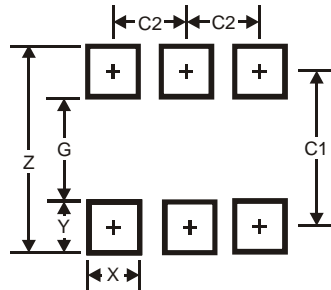
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
$\alpha$	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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